

Implantation of the ^{163}Ho Source for the ECHo Experiment



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T. Kieck^{1,3}, N. Kneip¹, D. Mowitz¹ and K. Wendt¹ for the ECHo Coll.*

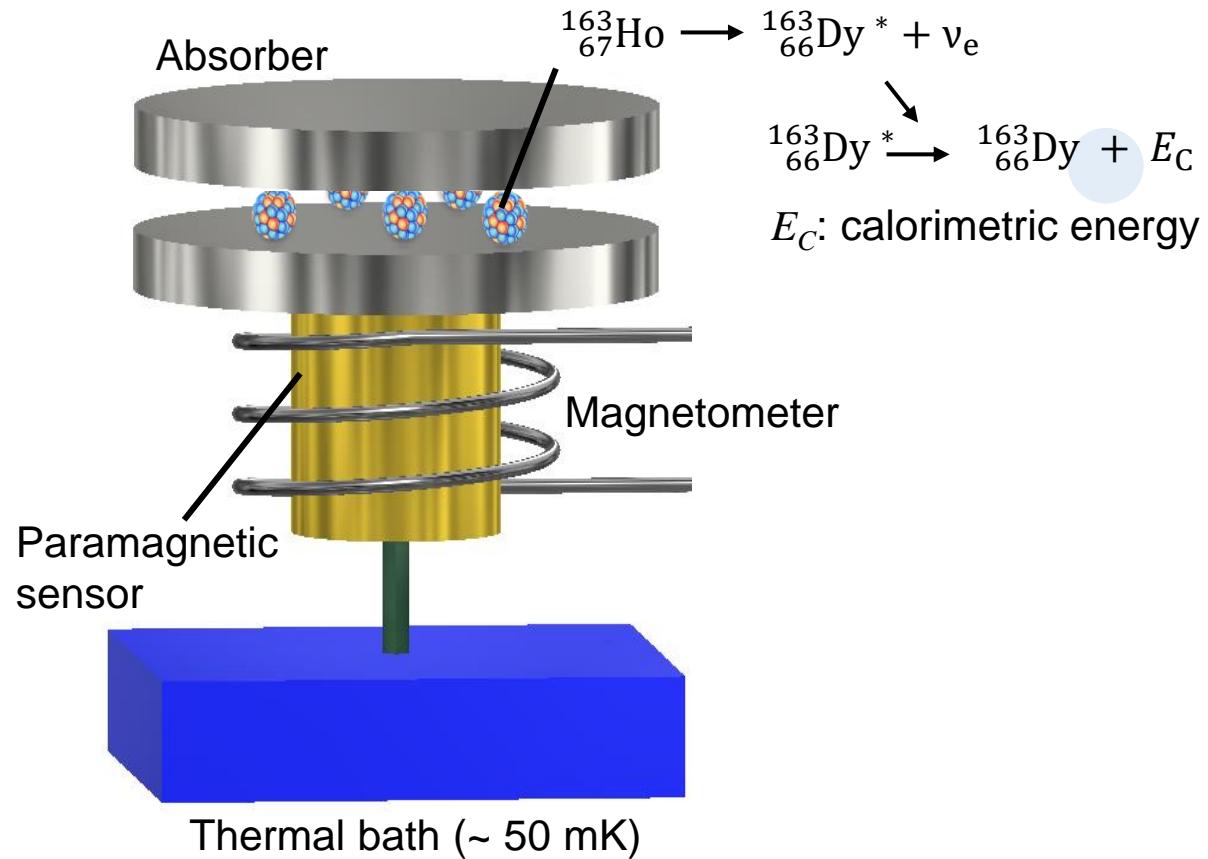
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The Electron Capture in ^{163}Ho Project

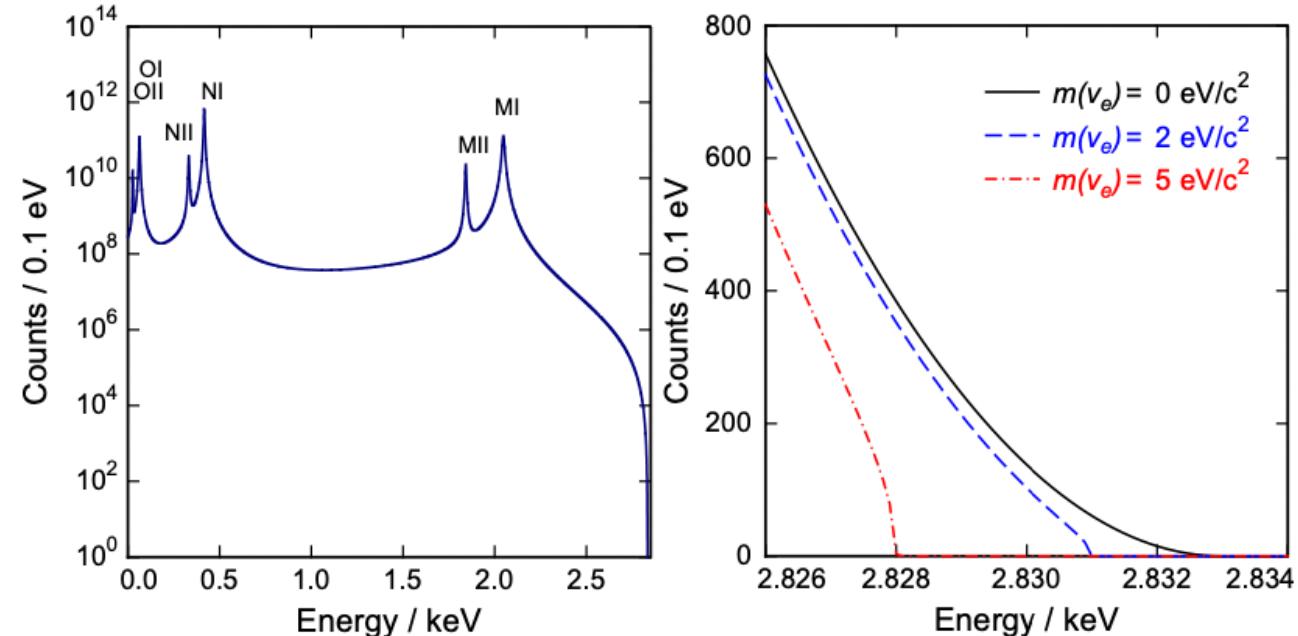


Schematics of the **Metallic Magnetic Calorimeter (MMC)** [1,2]

[1] A. De Rujula *et al.*, J. High Energ. Phys., **15**, 2016, 6.

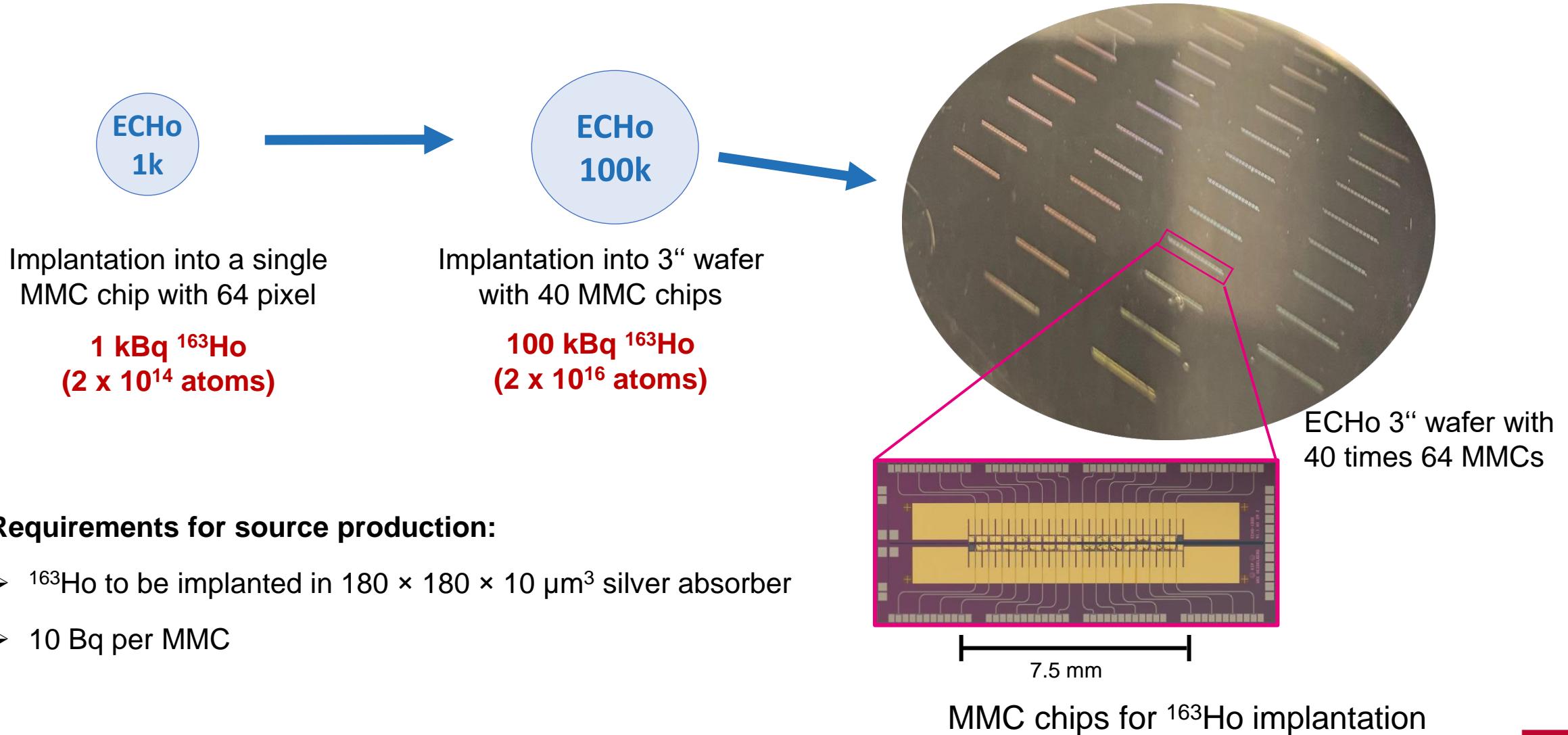
[2] L. Gastaldo *et al.*, Eur. Phys. J. Special Topics, **226**, 2017, 1623.

Deriving the neutrino mass from the decay spectrum



Calculated ^{163}Ho electron capture spectrum [2]

The Electron Capture in ^{163}Ho Project

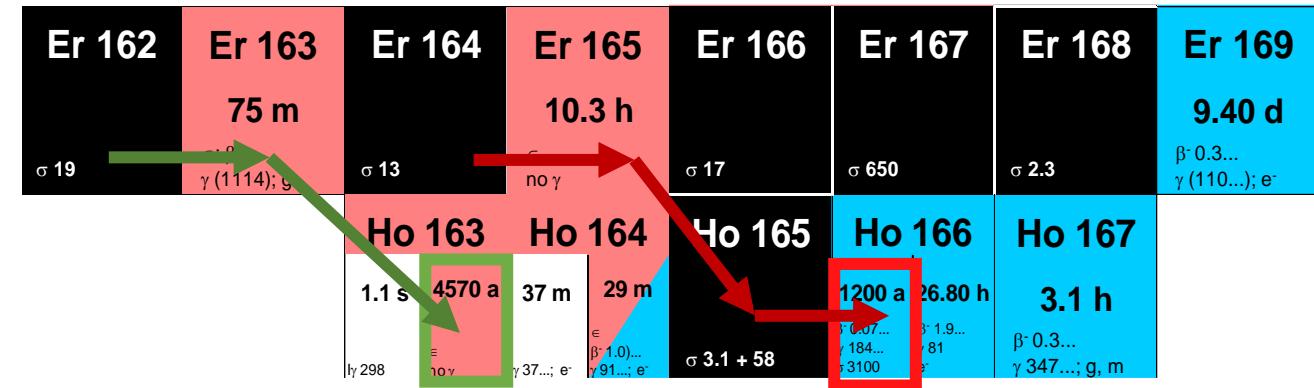


Production of ^{163}Ho at ILL Grenoble



High flux reactor at the ILL in Grenoble, France.
Thermal neutron flux: $\leq 1.5 \cdot 10^{15} \text{ n cm}^{-2} \text{ s}^{-1}$

Neutron irradiation of an enriched ^{162}Er target



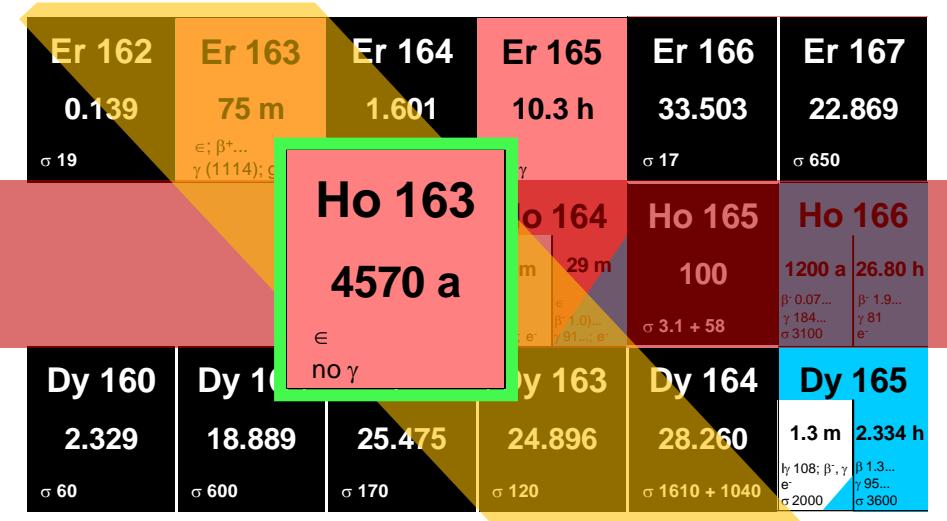
→ $\sim 6 \cdot 10^{18} \text{ }^{163}\text{Ho}$ atoms ($\sim 30 \text{ MBq}$) generated for implantation into Absorbers

Resonance Ionization Mass Spectrometry

Resonant laser ionization
Mass separation

Mono-isotopic ion beam

Resonant laser
ionization



Mass separation

Resonant laser ionization

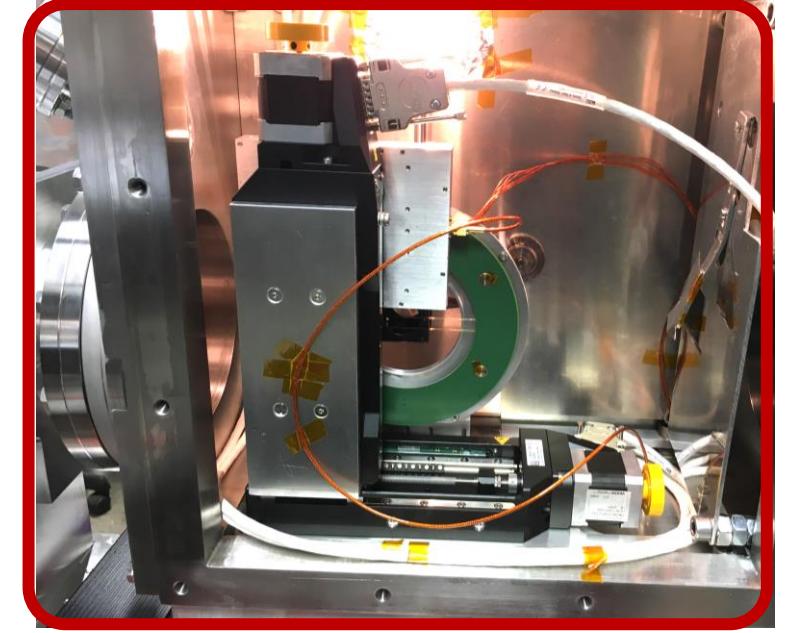
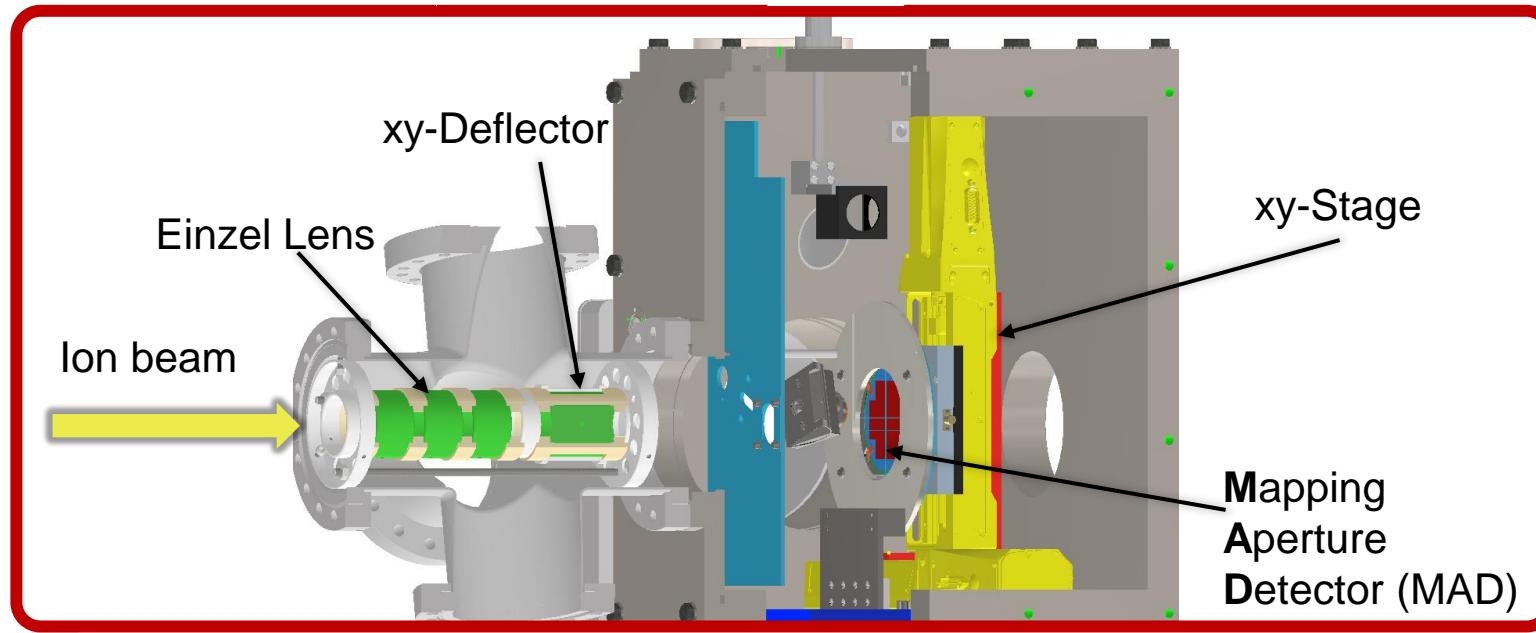
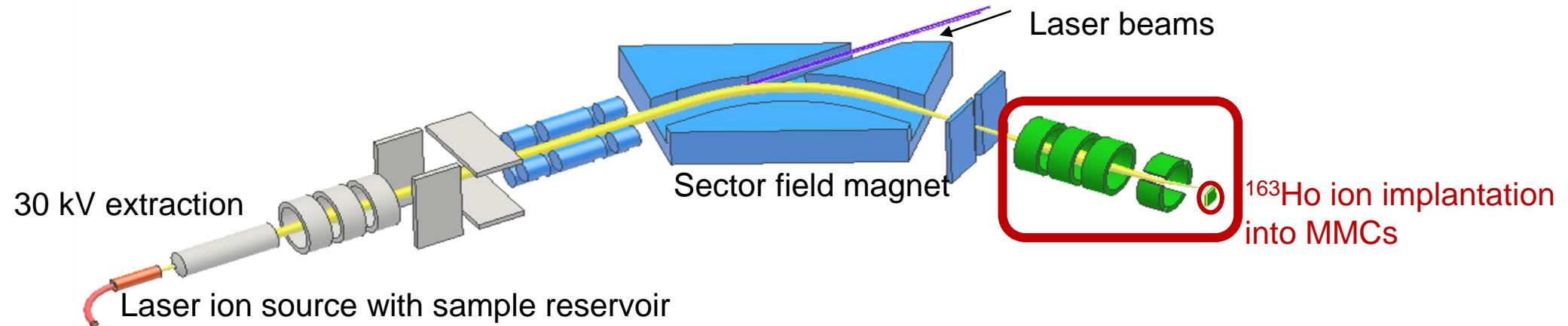


418.3 nm

405.5 nm

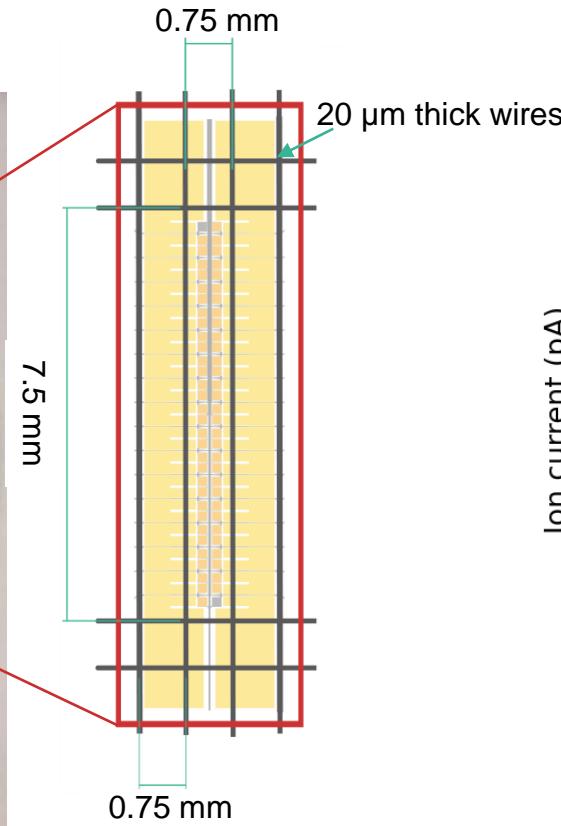
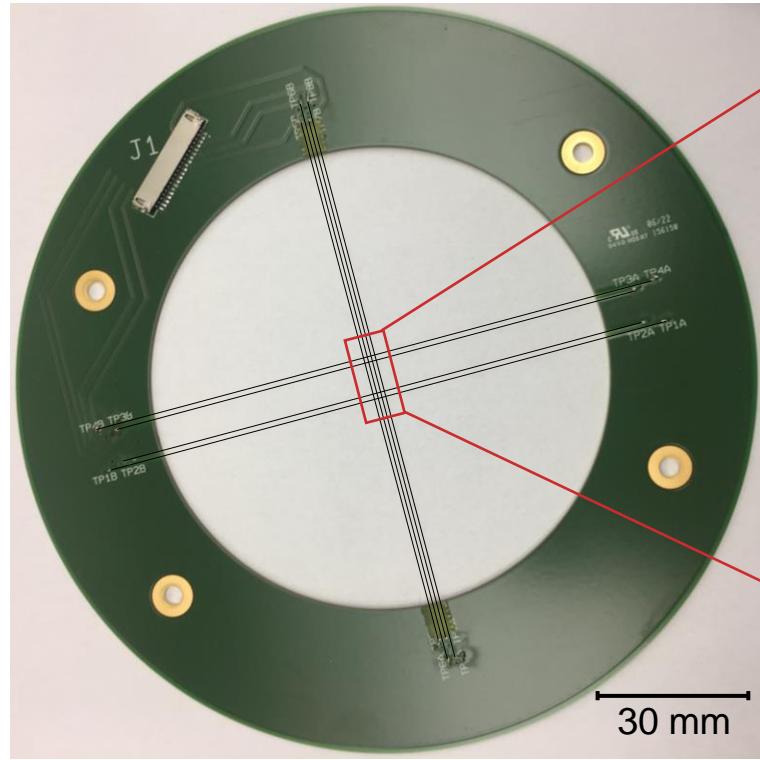
Efficiency: 69(9)% [1]

Mass separation and implantation at the RISIKO mass separator



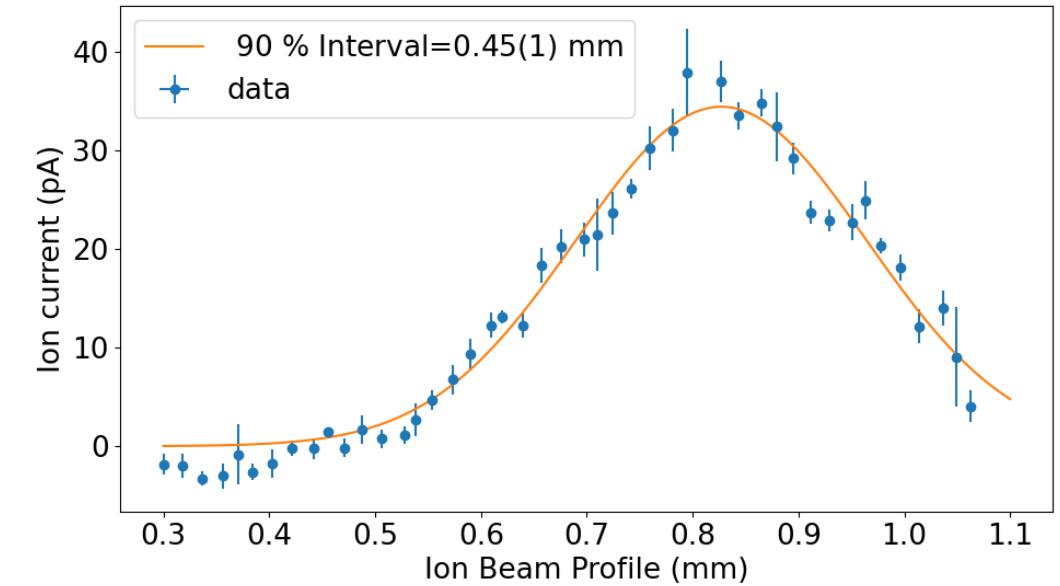
Mapping Aperture Detector

- Optimization and permanent ion beam control
- Ion beam characterization



Ion beam profile

Ion current: 20 nA



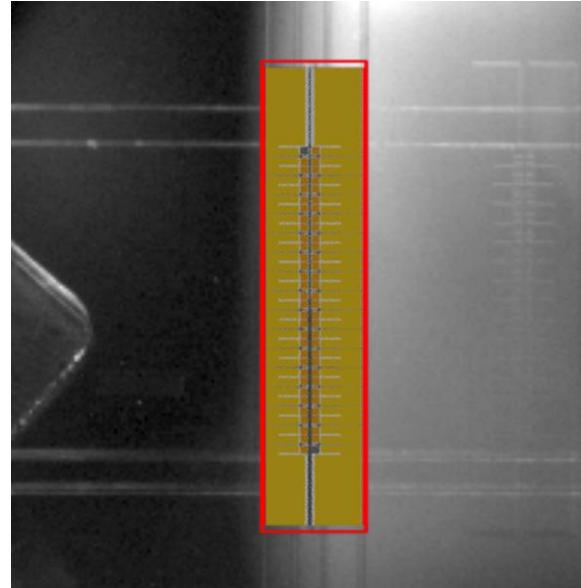
Implantation of an ECHo-100k wafer with ^{177}Lu

Verification of implantation accuracy by autoradiography

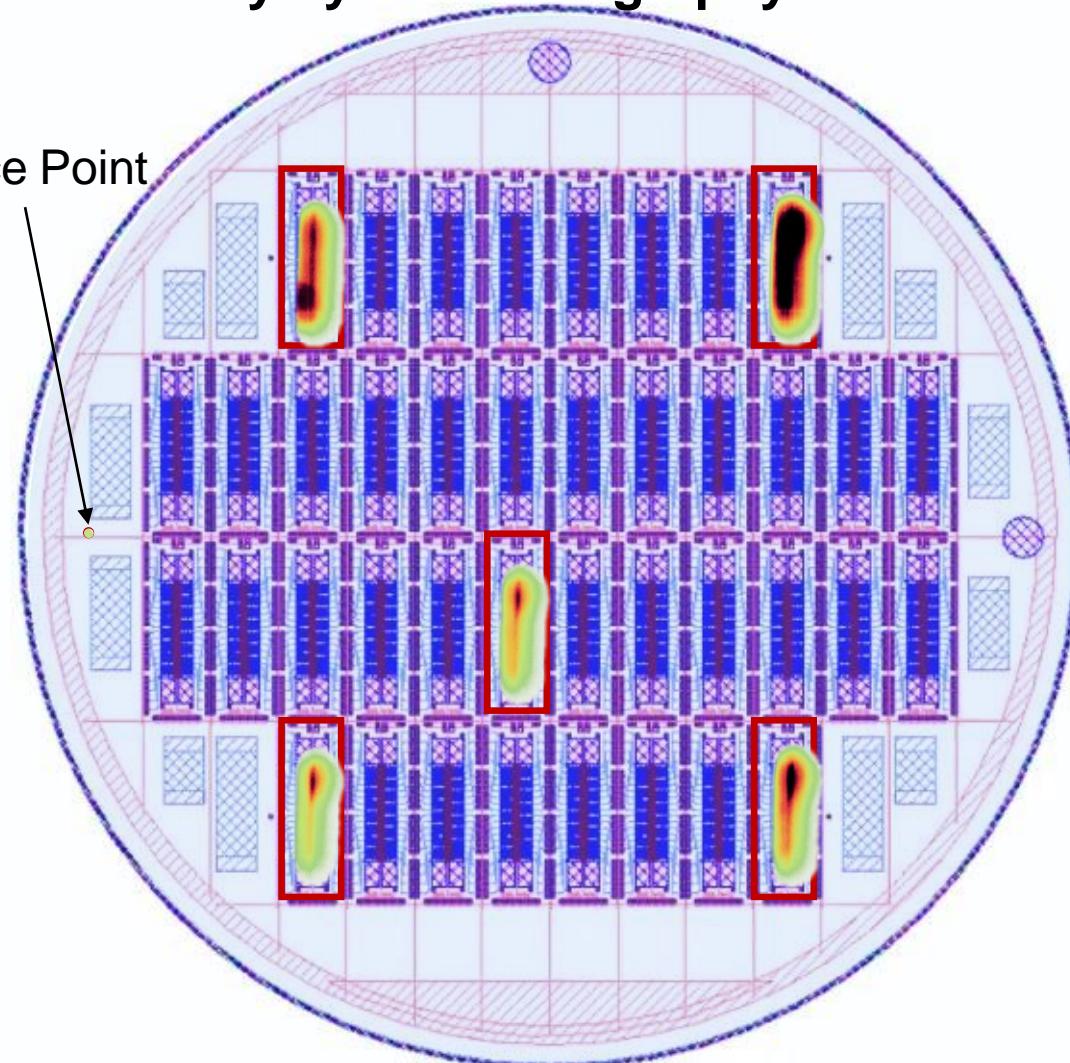
First implantation of a 3“ wafer at RISIKO

Lu 175	Lu 176	Lu 177
97.40	2.60	6.65 d

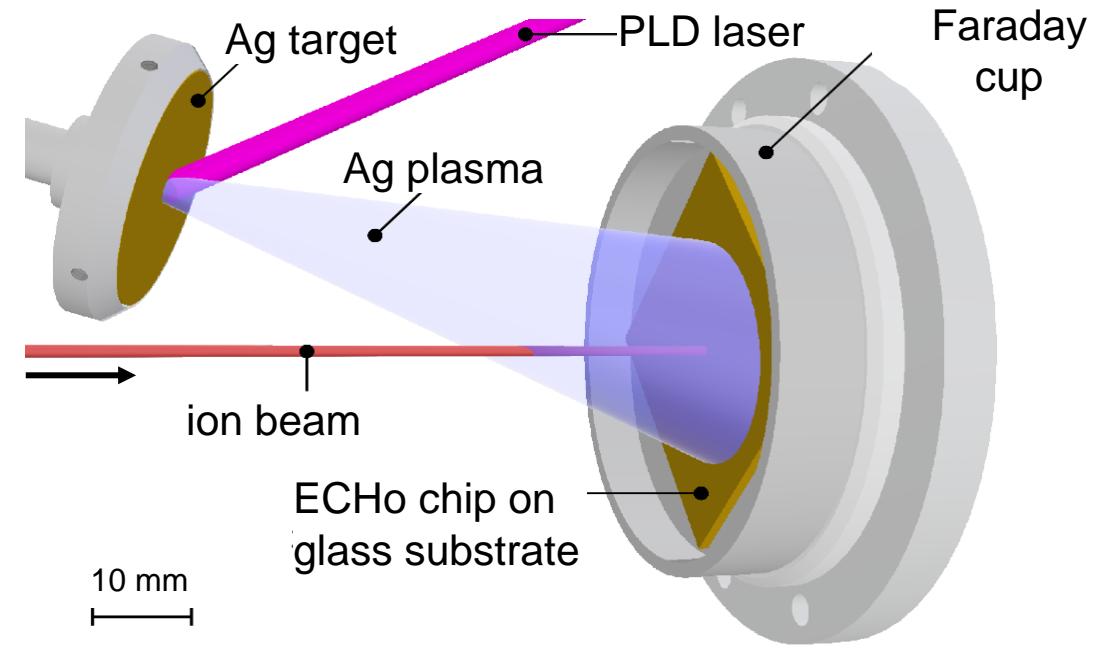
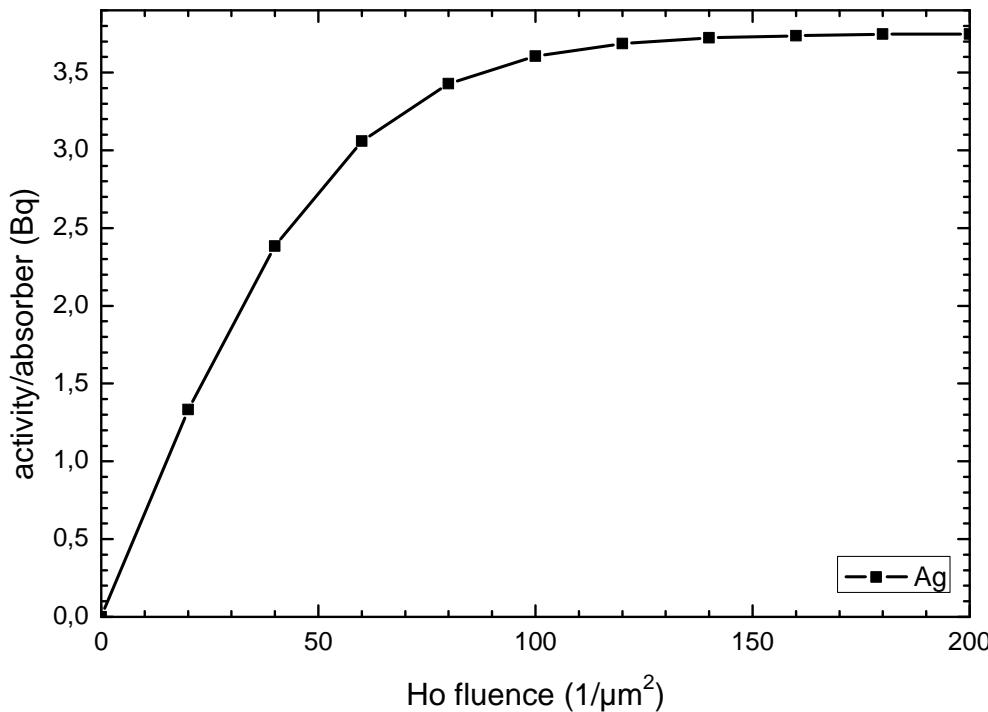
Position adjustment of the wafer with xy-Stage



Reference Point



Pulsed Laser Deposition (PLD)



TRIDYN Simulation for Ho implantation in Ag [1]

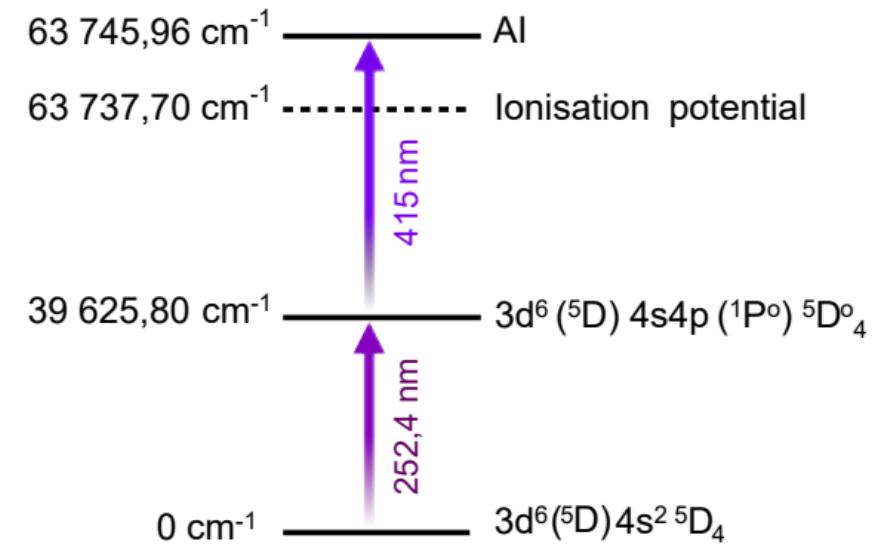
- Sputtering effects by ions with 30 kV
- 10 Bq per detector pixel
- PLD of 120 nm silver layer to compensate for sputtering effects
- Simultaneous deposition + ion implantation

Sketch of PLD setup [2]

[1] M. Möller *et al.*, Nuclear Inst. and Methods in Physics Research B, 2, 1984, 814.
[2] T. Kieck, PhD Thesis, 2019, JGU.

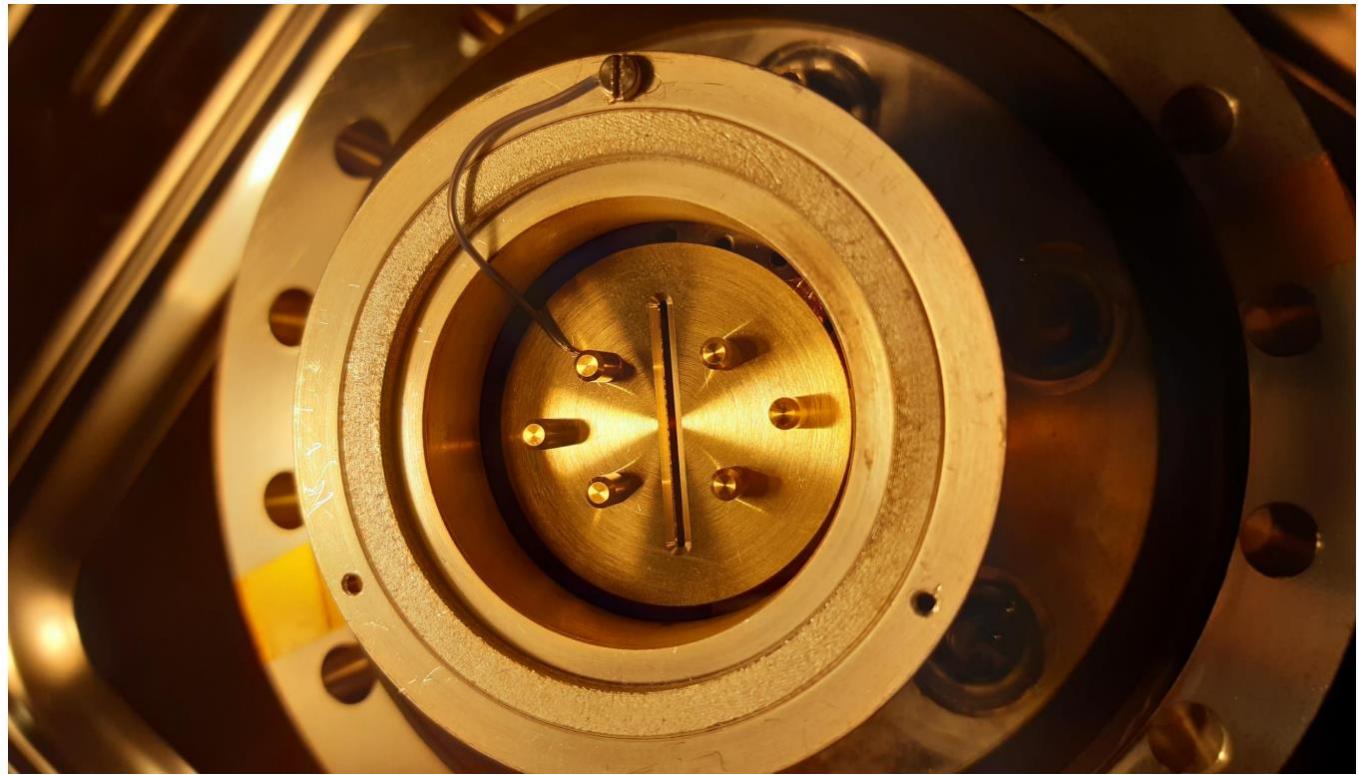
Implantation of ^{55}Fe into Absorbers

- Study of electron capture decay of ^{55}Fe for activity standardisation (Prima-LTD project)
- Goal: Implantation of 5 Bq per MMC pixel at RISIKO
- Two step elemental selective laser excitation scheme



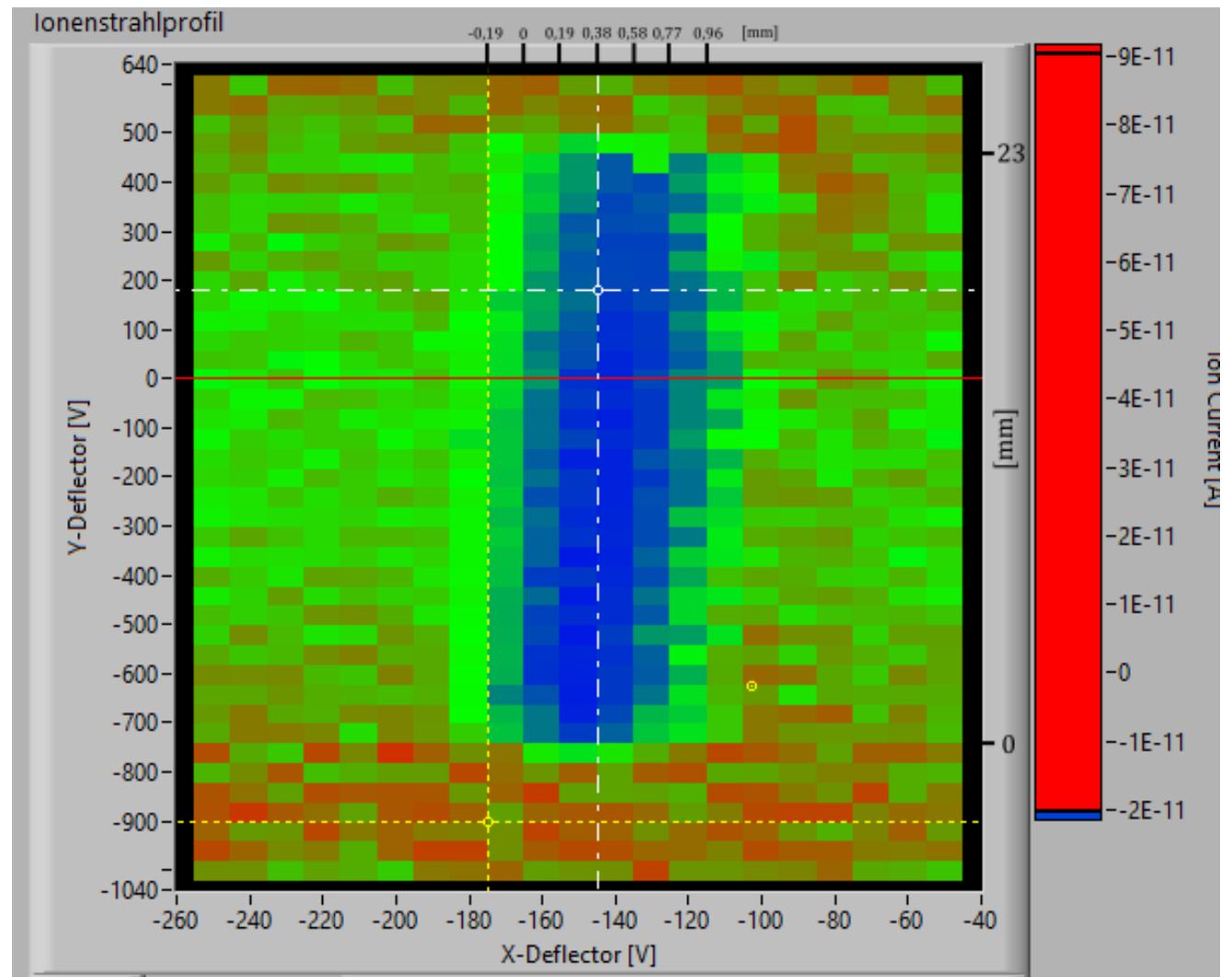
Implantation of ^{55}Fe

- Implantation without PLD
- Conductive aperture for beam alignment
- Current on aperture measured



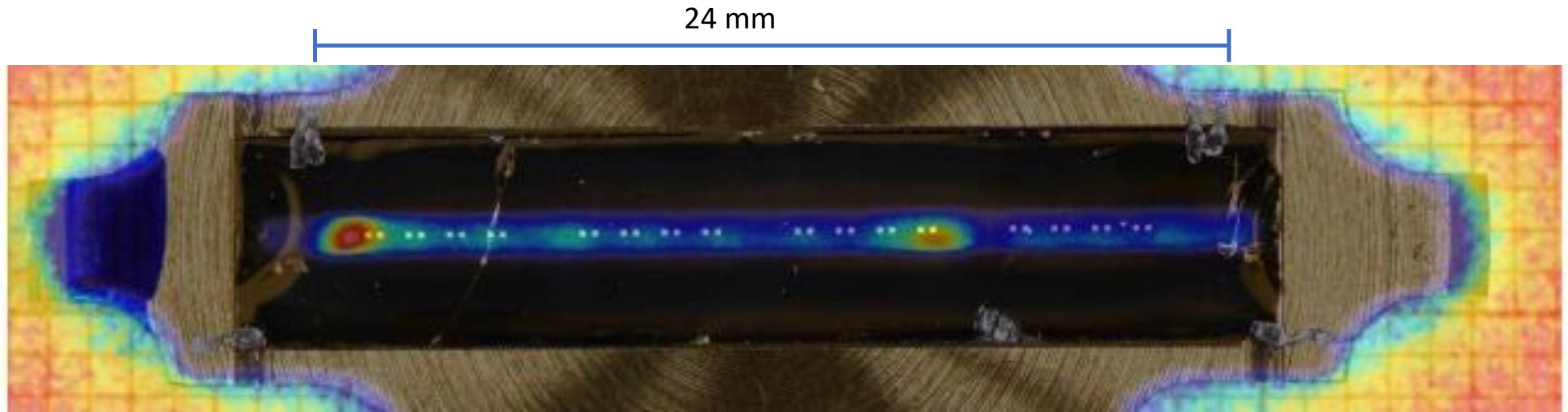
Implantation of ^{55}Fe

- Implantation without PLD
- Conductive aperture for beam alignment
- Current on aperture measured



Implantation of ^{55}Fe

- Implantation result of
- Goal: 1 Bq per pixel
- Beamwidth < 1 mm



Conclusion

- High ionization efficiency of Ho at RISIKO
→ 70 %
- Implantation region of RISIKO upgraded for 3" wafer implantation
- Demonstration of the implantation quality on 3" wafers
→ Implantation of ^{177}Lu and autoradiography
- First implantation of ^{163}Ho into a 3" wafer – complications with PLD
- Successfull implantation of ^{55}Fe into 24 MMCs (no PLD required)



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PrimA-LTD collaboration

M. Piel - Department of Chemistry – TRIGA Side, JGU Mainz

Thank you for your attention

